

Quad 2-Input Register

Features

- Function, pinout and drive compatible with FCT and F logic
- FCT-C speed at 6.1 ns max. (Com'l)
- FCT-A speed at 7.0 ns max. (Com'l)
- Reduced V_{OH} (typically = 3.3V) versions of equivalent FCT functions
- Edge-rate control circuitry for significantly improved noise characteristics
- Power-off disable feature
- Matched rise and fall times

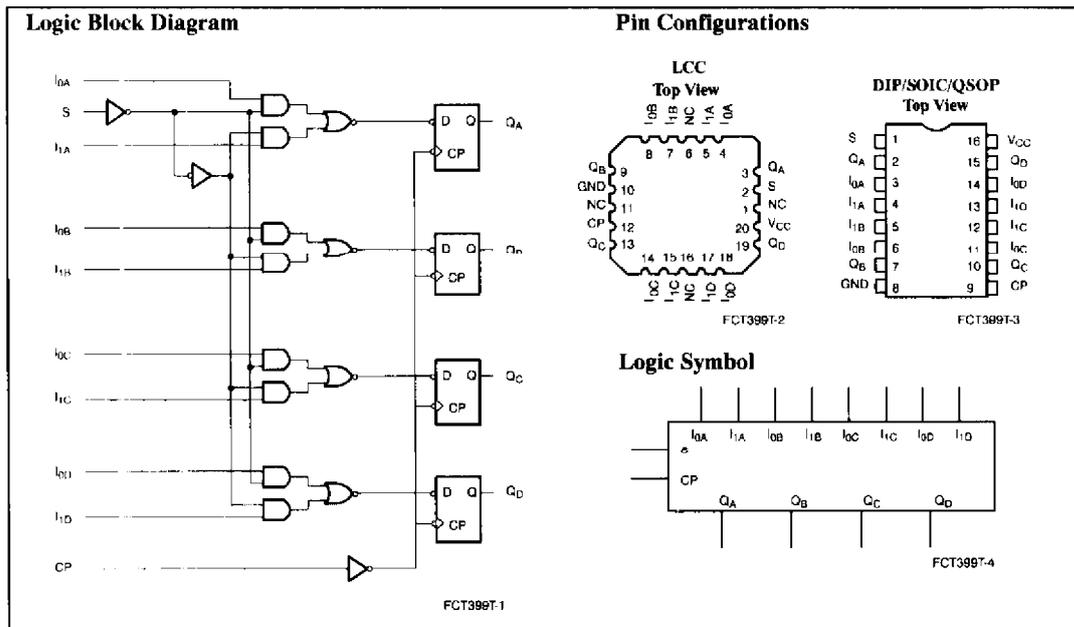
- ESD > 2000V
- Fully compatible with TTL input and output logic levels
- Sink current 64 mA (Com'l), 32 mA (Mil)
- Source current 32 mA (Com'l), 12 mA (Mil)

Functional Description

The FCT399T is a high-speed quad dual-port register that selects four bits of data from either of two sources (Ports) under control of a common Select input

(S). The selected data is transferred to a 4-bit output register synchronous with the LOW-to-HIGH transition of the Clock input (CP). The 4-bit D-type output register is fully edge-triggered. The Data inputs (I_0X , I_1X) and Select input (S) must be stable only one set-up time prior to, and hold time after, the LOW-to-HIGH transition of the Clock input for predictable operation. The FCT399T offers true outputs.

The outputs are designed with a power-off disable feature to allow for live insertion of boards.



Pin Description

Name	Description
S	Common Select Input
CP	Clock Pulse Input (Active Rising Edge)
I_0	Data Inputs from Source 0
I_1	Data Inputs from Source 1
Q	Register True Outputs

Function Table⁽¹⁾

Inputs			Outputs
S	I_0	I_1	Q
l	l	X	L
l	h	X	H
h	X	l	L
h	X	h	H

Note:

1. H = HIGH Voltage Level
h = HIGH Voltage Level one set-up time prior to the LOW-to-HIGH Clock Transition
L = LOW Voltage Level
l = LOW Voltage Level one set-up time prior to the LOW-to-HIGH Clock Transition
X = Don't Care



Maximum Ratings^(2, 3)

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature -65°C to +150°C
 Ambient Temperature with Power Applied -65°C to +135°C
 Supply Voltage to Ground Potential -0.5V to +7.0V
 DC Input Voltage -0.5V to +7.0V
 DC Output Voltage 0.5V to +7.0V
 DC Output Current (Maximum Sink Current/Pin) 120 mA
 Power Dissipation 0.5W

Static Discharge Voltage >2001V
 (per MIL-STD-883, Method 3015)

Operating Range

Range	Range	Ambient Temperature	V _{CC}
Commercial	CT	0°C to +70°C	5V ± 5%
Commercial	T, AT	40°C to +85°C	5V ± 5%
Military ⁽⁴⁾	All	-55°C to +125°C	5V ± 10%

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions	Min.	Typ. ⁽⁵⁾	Max.	Unit
V _{OHI}	Output HIGH Voltage	V _{CC} = Min., I _{OHI} = -32 mA, Com'l	2.0			V
		V _{CC} = Min., I _{OHI} = -15 mA, Com'l	2.4	3.3		V
		V _{CC} = Min., I _{OHI} = -12 mA, Mil	2.4	3.3		V
V _{OL}	Output LOW Voltage	V _{CC} = Min., I _{OL} = 64 mA, Com'l		0.3	0.55	V
		V _{CC} = Min., I _{OL} = 32 mA, Mil		0.3	0.55	V
V _{IHI}	Input HIGH Voltage		2.0			V
V _{IL}	Input LOW Voltage				0.8	V
V _h	Hysteresis ⁽⁶⁾	All inputs		0.2		V
V _{IK}	Input Clamp Diode Voltage	V _{CC} = Min., I _{IN} = -18 mA		-0.7	-1.2	V
I _H	Input HIGH Current	V _{CC} = Max., V _{IN} = V _{CC}			5	µA
I _{IHI}	Input HIGH Current	V _{CC} = Max., V _{IN} = 2.7V			±1	µA
I _{IL}	Input LOW Current	V _{CC} = Max., V _{IN} = 0.5V			±1	µA
I _{OS}	Output Short Circuit Current ⁽⁷⁾	V _{CC} = Max., V _{OUT} = 0.0V	-60	-120	-225	mA
I _{on}	Power-Off Disable	V _{CC} = 0V, V _{OUT} = 4.5V			±1	µA

Capacitance⁽⁶⁾

Parameter	Description	Typ. ⁽⁵⁾	Max.	Unit
C _{IN}	Input Capacitance	5	10	pF
C _{OUT}	Output Capacitance	9	12	pF

Notes:

- Unless otherwise noted, these limits are over the operating free-air temperature range.
- Unused inputs must always be connected to an appropriate logic voltage level, preferably either V_{CC} or ground.
- T_A is the "instant on" case temperature.
- Typical values are at V_{CC} = 5.0V, T_A = +25°C ambient.
- This parameter is guaranteed but not tested.
- Not more than one output should be shorted at a time. Duration of short should not exceed one second. The use of high-speed test apparatus and/or sample and hold techniques is preferable in order to minimize internal chip heating and more accurately reflect operational values. Otherwise prolonged shorting of a high output may raise the chip temperature well above normal and thereby cause invalid readings in other parametric tests. In any sequence of parameter tests, I_{OS} tests should be performed last.

Power Supply Characteristics

Parameter	Description	Test Conditions	Typ. ^[5]	Max.	Unit
I_{CC}	Quiescent Power Supply Current	$V_{CC} = \text{Max.}, V_{IN} \leq 0.2V,$ $V_{IN} \geq V_{CC} - 0.2V$	0.1	0.2	mA
ΔI_{CC}	Quiescent Power Supply Current (TTL inputs)	$V_{CC} = \text{Max.}, V_{IN} = 3.4V$ ^[8] $f_1 = 0, \text{Outputs Open}$	0.5	2.0	mA
$I_{CC(D)}$	Dynamic Power Supply Current ^[9]	$V_{CC} = \text{Max.}, \text{One Input Toggling},$ $50\% \text{ Duty Cycle, Outputs Open},$ $V_{IN} \leq 0.2V \text{ or } V_{IN} \geq V_{CC} - 0.2V$	0.06	0.12	mA/ MHz
I_C	Total Power Supply Current ^[10]	$V_{CC} = \text{Max.}, f_0 = 10 \text{ MHz},$ $50\% \text{ Duty Cycle, Outputs Open},$ $\text{One Input Toggling at } f_1 = 5 \text{ MHz},$ $S = \text{Steady State}$ $V_{IN} \leq 0.2V \text{ or } V_{IN} \geq V_{CC} - 0.2V$	0.7	1.4	mA
		$V_{CC} = \text{Max.}, f_0 = 10 \text{ MHz},$ $50\% \text{ Duty Cycle, Outputs Open},$ $\text{One Input Toggling at } f_1 = 5 \text{ MHz},$ $S = \text{Steady State}$ $V_{IN} = 3.4V \text{ or } V_{IN} = \text{GND}$	1.2	3.4	mA
		$V_{CC} = \text{Max.}, f_0 = 10 \text{ MHz},$ $50\% \text{ Duty Cycle, Outputs Open},$ $\text{Four Inputs Toggling at } f_1 = 5 \text{ MHz},$ $S = \text{Steady State}$ $V_{IN} \leq 0.2V \text{ or } V_{IN} \geq V_{CC} - 0.2V$	1.6	3.2 ^[11]	mA
		$V_{CC} = \text{Max.}, f_0 = 10 \text{ MHz},$ $50\% \text{ Duty Cycle, Outputs Open},$ $\text{Four Inputs Toggling at } f_1 = 5 \text{ MHz},$ $S = \text{Steady State}$ $V_{IN} = 3.4V \text{ or } V_{IN} = \text{GND}$	2.9	8.2 ^[11]	mA

Notes:

8. Per TTL driven input ($V_{IN} = 3.4V$); all other inputs at V_{CC} or GND.
 9. This parameter is not directly testable, but is derived for use in Total Power Supply calculations.
 10. $I_C = I_{\text{QUIESCIENT}} + I_{\text{INPUTS}} + I_{\text{DYNAMIC}}$
 $I_C = I_{CC} + \Delta I_{CC} D_{H1} N_1 + I_{CC(D)} (f_0/2 + f_1 N_1)$
 I_{CC} = Quiescent Current with CMOS input levels
 ΔI_{CC} = Power Supply Current for a TTL HIGH input ($V_{IN} = 3.4V$)
 D_{H1} = Duty Cycle for TTL inputs HIGH

- N_1 = Number of TTL inputs at D_{H1}
 $I_{CC(D)}$ = Dynamic Current caused by an input transition pair (HLH or LHL)
 f_0 = Clock frequency for registered devices, otherwise zero
 f_1 = Input signal frequency
 N_1 = Number of inputs changing at f_1
 All currents are in milliamps and all frequencies are in megahertz.
 11. Values for these conditions are examples of the I_{CC} formula. These limits are guaranteed but not tested.



Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
6.1	CY74FCT399CTPC	P1	16-Lead (300-Mil) Molded DIP	Commercial
	CY74FCT399CTQC	Q1	16-Lead (150-Mil) QSOP	
	CY74FCT399CTSOC	S1	16-Lead (300-Mil) Molded SOIC	
6.6	CY54FCT399CTDMB	D2	16-Lead (300-Mil) CerDIP	Military
	CY54FCT399CTLMB	L61	20-Pin Square Leadless Chip Carrier	
7.0	CY74FCT399ATPC	P1	16-Lead (300-Mil) Molded DIP	Commercial
	CY74FCT399ATQC	Q1	16-Lead (150-Mil) QSOP	
	CY74FCT399ATSOC	S1	16-Lead (300-Mil) Molded SOIC	
7.5	CY54FCT399ATDMB	D2	16-Lead (300-Mil) CerDIP	Military
	CY54FCT399ATLMB	L61	20-Pin Square Leadless Chip Carrier	
10.0	CY74FCT399TPC	P1	16-Lead (300-Mil) Molded DIP	Commercial
	CY74FCT399TQC	Q1	16-Lead (150-Mil) QSOP	
	CY74FCT399TSOC	S1	16-Lead (300-Mil) Molded SOIC	
11.5	CY54FCT399TDMB	D2	16-Lead (300-Mil) CerDIP	Military
	CY54FCT399TLMB	L61	20-Pin Square Leadless Chip Carrier	

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Ordering Information

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6.1	CY74FCT399CTPC	P1	16-Lead (300-Mil) Molded DIP	Commercial
	CY74FCT399CTQC	Q1	16-Lead (150-Mil) QSOP	
	CY74FCT399CTSOC	S1	16-Lead (300-Mil) Molded SOIC	
6.6	CY54FCT399CTDMB	D2	16-Lead (300-Mil) CerDIP	Military
	CY54FCT399CTLMB	L61	20-Pin Square Leadless Chip Carrier	
7.0	CY74FCT399ATPC	P1	16-Lead (300-Mil) Molded DIP	Commercial
	CY74FCT399ATQC	Q1	16-Lead (150-Mil) QSOP	
	CY74FCT399ATSOC	S1	16-Lead (300-Mil) Molded SOIC	
7.5	CY54FCT399ATDMB	D2	16-Lead (300-Mil) CerDIP	Military
	CY54FCT399ATLMB	L61	20-Pin Square Leadless Chip Carrier	
10.0	CY74FCT399TPC	P1	16-Lead (300-Mil) Molded DIP	Commercial
	CY74FCT399TQC	Q1	16-Lead (150-Mil) QSOP	
	CY74FCT399TSOC	S1	16-Lead (300-Mil) Molded SOIC	
11.5	CY54FCT399TDMB	D2	16-Lead (300-Mil) CerDIP	Military
	CY54FCT399TLMB	L61	20-Pin Square Leadless Chip Carrier	

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